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Hong-ki Kim received his B.S., M.S., and Ph.D. degrees in Electronic Materials Engineering from Kwangwoon University in 2010, 2012, and 2016, respectively. From 2017 to 2020, he worked in POSTECH-Fraunhofer IISB Research Center in National Institute for Nanomaterials Technology (NINT). Since 2020, he is engineer for SiC MOSFET development in Powermaster Semiconductor. Regarding his research field, he has authored or co-authored more than 40 SCI papers and applied more than 10 patents.